

General Purpose Transistor

NPN Silicon

PZT3904T1G

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

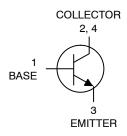
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	40	Vdc
Collector - Base Voltage	V_{CBO}	60	Vdc
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	200	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) T _A = 25°C	P _D	1.5 12	W mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	°C/W
Thermal Resistance Junction-to-Lead #4	$R_{\theta JA}$	35	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

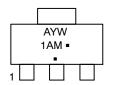
^{1.} FR-4 with 1 oz and 713 mm^2 of copper area.





SOT-223 CASE 318E STYLE 1

MARKING DIAGRAM



1AM = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
PZT3904T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZT3904T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

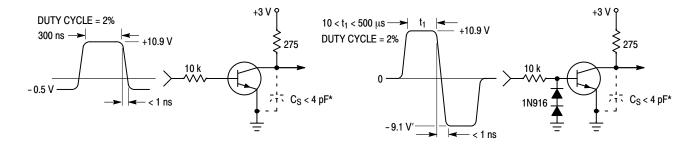
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Chara	acteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note 2)			•	•	•
Collector - Emitter Breakdown Voltage (N	ote 3) (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	40	-	Vdc
Collector - Base Breakdown Voltage (I _C =	= 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	1
Emitter – Base Breakdown Voltage (I _E = 1	0 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	1
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB}$	= 3.0 Vdc)	I _{BL}	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, \	/ _{EB} = 3.0 Vdc)	I _{CEX}	-	50	1
ON CHARACTERISTICS (Note 3)					
$\begin{array}{l} \text{DC Current Gain (Note 2)} \\ \text{(I}_{\text{C}} = 0.1 \text{ mAdc, } V_{\text{CE}} = 1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = 1.0 \text{ mAdc, } V_{\text{CE}} = 1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = 1.0 \text{ mAdc, } V_{\text{CE}} = 1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = 10 \text{ mAdc, } V_{\text{CE}} = 1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = 50 \text{ mAdc, } V_{\text{CE}} = 1.0 \text{ Vdc)} \\ \text{(I}_{\text{C}} = 100 \text{ mAdc, } V_{\text{CE}} = 1.0 \text{ Vdc)} \end{array}$		H _{FE}	40 70 100 60 30	- 300 - -	-
Collector – Emitter Saturation Voltage (No $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	ote 3)	V _{CE(sat)}	- -	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (Note 3 ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	3)	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C =	10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_{E} =$	0, f = 1.0 MHz)	C _{obo}	-	5.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0.6 \text{ Vdc}$, f = 1.0 MHz)	C _{ibo}	-	8.0	
Input Impedance ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 1.0 \text{ Vdc}$	mAdc, f = 1.0 kHz)	h _{ie}	1.0	10	kΩ
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I	C = 1.0 mAdc, f = 1.0 kHz)	h _{re}	0.5	8.0	X 10 ⁻⁴
Small – Signal Current Gain (V _{CE} = 10 Vo	lc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{fe}	100	400	-
Output Admittance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)		h _{oe}	1.0	40	μMhos
Noise Figure (V_{CE} = 5.0 Vdc, I_{C} = 100 μ Adc, R_{S} = 1.0 $k\Omega$, f = 1.0 kHz)		nF	-	5.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc,	t _d	-	35	ns
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	=	35	1
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	-	200	1
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc}$	t _f	-	50	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} FR-5 = 1.0 \times 0.75 \times 0.062 in. 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

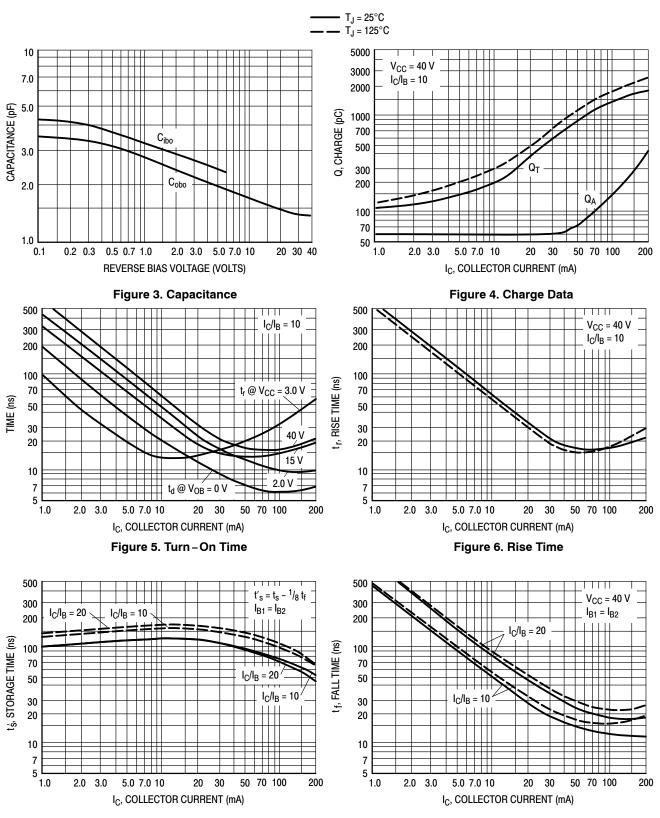
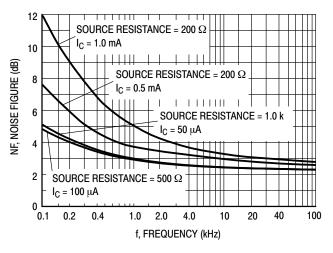


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ VDC}, T_A = 25^{\circ}\text{C}, BANDWIDTH = 1.0 \text{ HZ})$



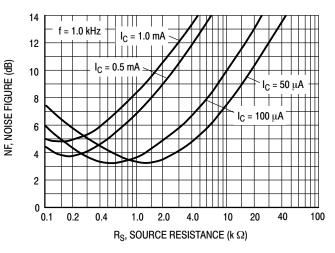
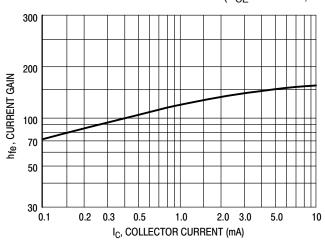


Figure 9.

Figure 10.

H PARAMETERS

(V_{CE} = 10 VDC, F = 1.0 KHZ, T_A = 25°C)



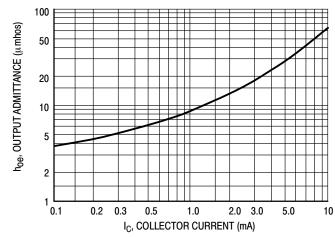
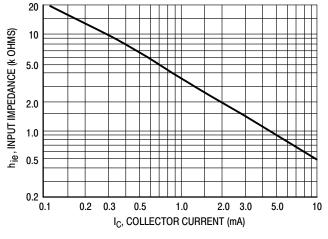


Figure 11. Current Gain

Figure 12. Output Admittance





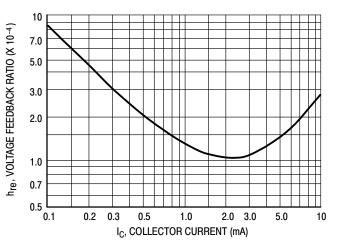


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

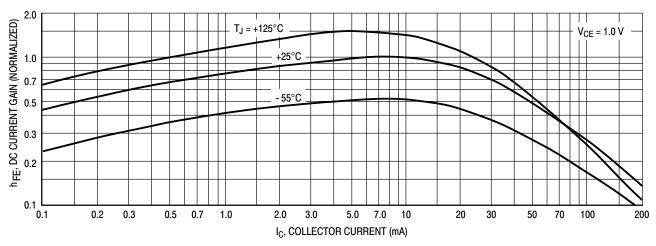


Figure 15. DC Current Gain

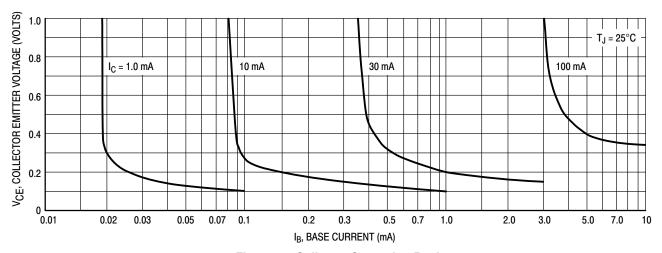


Figure 16. Collector Saturation Region

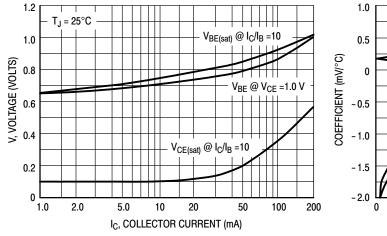


Figure 17. "ON" Voltages

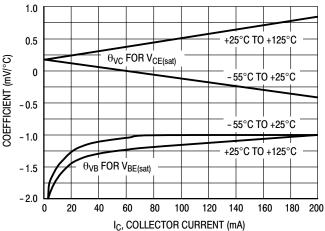


Figure 18. Temperature Coefficients

TYPICAL CHARACTERISTICS

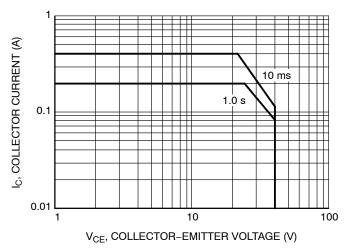


Figure 19. Safe Operating Area

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